

NPN Silicon Planar High Voltage Transistor

FEATURES

- High BV_{CEO}, BV_{CBO}
- High current gain
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-Free according to IEC 61249-2-21

APPLICATION

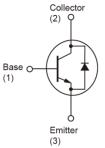
- Lighting
- Switch mode power supply

KEY PERFORMANCE PARAMETERS				
PA	RAMETER	VALUE	UNIT	
	BV _{CEO}	400	V	
	BV _{CBO}	600	V	
	I _C	300	mA	
V _{CE(SAT)}	I _C =50mA, I _B =5mA	0.5	V	









Notes: MSL 3 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Collector-Base Voltage		V _{CBO}	600	V	
Collector-Emitter Voltage		V _{CES}	600	V	
Collector-Emitter Voltage @ V _{BE} =0V		V _{CES}	400	V	
Emitter-Base Voltage		V _{EBO}	7	V	
	DC		0.3	А	
Collector Current	Pulse	l _c	1	А	
Power Total Dissipation @ T _A =25°C		P _{DTOT}	1	W	
Maximum Operating Junction Temperature		TJ	+150	°C	
Storage Temperature Range		T _{STG}	-55 to +150	°C	

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction to Ambient Thermal Resistance	R _{eja}	91	°C/W	
Junction to Case Thermal Resistance	R _{eJC}	25	°C/W	



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ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	ТҮР	MAX	UNIT
Static (Note 1)						
Collector-Base voltage	I _C =50μA	BV _{CBO}	600			V
Collector-Emitter Saturation Voltage	I _C =100μA, V _{BE} =0	BV _{CES}	600			V
Collector-Emitter breakdown voltage	I _C =1mA	BV _{CEO}	400			V
Emitter-Base breakdown voltage	I _E =50μA	BV _{EBO}	7			V
Emitter cut-off current	V _{EB} =7V	I _{EBO}			1.5	μA
Collector cut-off current	V _{CB} =600V	I _{CBO}			0.5	μA
Collector-Emitter Cutoff Current	V _{CE} =400V	I _{CEO}			1	μA
Collector-Emitter saturation voltage	I _C =50mA, I _B =5mA	V _{CE(SAT)}			0.5	V
Base-Emitter saturation voltage	I _C =50mA, I _B =5mA	V _{BE(SAT)}			1	V
DC Current Gain	V_{CE} =5V, I_C =1mA	h _{FE} 1	100			
	$V_{CE} = 5V, I_{C} = 20mA$	h _{FE} 2	90		300	
Transition Frequency	$V_{CE} = 10V, I_E = 20mA$	f _T	50			MHz
Output Capacitance	V _{CB} =20V, f =1MHz	Cob			7	pF

Notes:

1. Pulse test: \leq 380µs, duty cycle \leq 2%

2. For DESIGN AID ONLY, not subject to production testing.

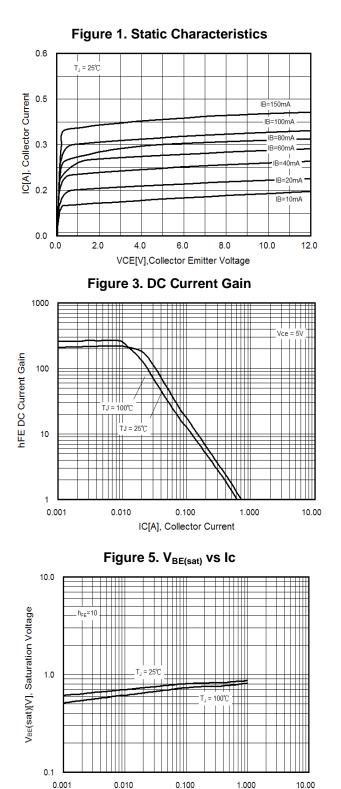
ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSC966CW RPG	SOT-223	2,500pcs / 13"Reel

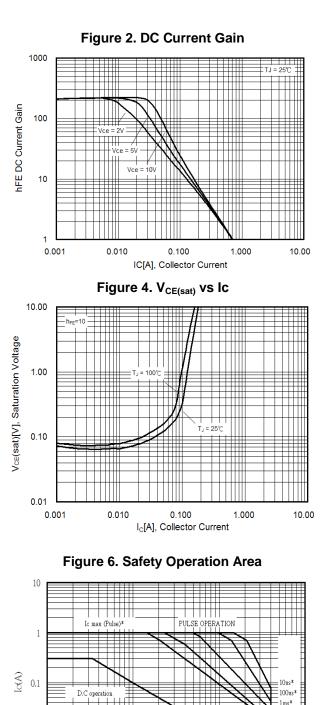


Electrical Characteristics Curve

(Ta = 25°C, unless otherwise noted)



I_C[A], Collector Current



Т

10

Curve must be derated linearly with increase in temperature.

Single nonrepetitive pulse Tamb=25 °C 10ms 100ms

. DC

1000

100

V_{CE}(V)

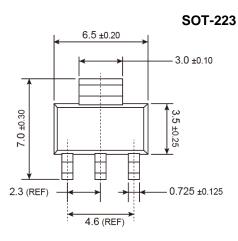
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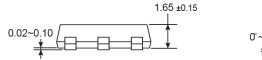
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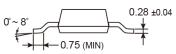
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PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



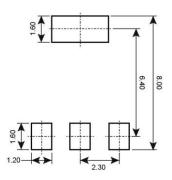




SUGGESTED PAD LAYOUT (Unit: Millimeters)

Υ

Μ



Marking Diagram



= Year Code	;				
= Month Code for Halogen Free Product					
O =Jan	P =Feb	Q =Mar	R =Apr		
S =May	T =Jun	U =Jul	V =Aug		
W =Sep	X =Oct	Y =Nov	Z =Dec		

L = Lot Code



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